

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 242820US2RD		SERIAL NO. New Application	
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Yoshiaki SAITO, et al.					
		FILING DATE Herewith		GROUP			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	5,659,499	08/19/97	E. CHEN, et al.			
	AB	5,956,267	09/21/99	A. T. HURST, et al.			
	AC	5,734,605	03/31/98	X. T. ZHU, et al.			
	AD	5,640,343	06/17/97	W. J. GALLAGHER, et al.			
	AE	5,940,319	08/17/99	M. DURLAM, et al.			
	AF	6,351,408	02/26/2002	S. SCHWARZL, et al.			
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
					YES	NO	
	AO	WO 00/10172	02/24/2000	WIPO (with English Abstract)			X
	AP	10-4227	01/06/98	JAPAN (with English Abstract)			X
	AQ	WO 99/14760	03/25/99	WIPO (with English Abstract)			X
	AR	197 44 095	04/15/99	WIPO (with corr. US 6,351,408)			X
	AS						
	AT						
	AU						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AV	J. S. MOODERA, et al., "FERROMAGNETIC-INSULATOR-FERROMAGNETIC TUNNELING: SPIN-DEPENDENT TUNNELING AND LARGE MAGNETORESISTANCE IN TRILAYER JUNCTION (INVITED)", Vol. 79, No. 8, pgs. 4724-4729, J. Appl. Phys., April 15, 1996					
	AW	L. F. SCHELP, et al., "SPIN-DEPENDENT TUNNELING WITH COULOMB BLOCKADE", Vol. 56, No. 10, pgs. R5747-R5750, Physical Review B, September 1, 1997					
	AX	Y. SAITO, et al., "SPIN-DEPENDENT TUNNELING THROUGH LAYERED HARD-MAGNETIC-NANO-PARTICLES", Vol. 23, No. 4-2, pgs. 1269-1272, J. Jpn. Appl. Magn. Society, 1999 (with English Abstract)					
	AY	F. MONTAIGNE, et al., "ENHANCED TUNNEL MAGNETORESISTANCE AT HIGH BIAS VOLTAGE IN DOUBLE-BARRIER PLANAR JUNCTIONS", Vol. 73, No. 19, pgs. 2829-2831, Applied Physics Letters, November 9, 1998					
	AZ	Y. SAITO, et al., "CORRELATION BETWEEN BARRIER WIDTH, BARRIER HEIGHT, AND DC BIAS VOLTAGE DEPENDENCES ON THE MAGNETORESISTANCE RATIO IN Ir-Mn EXCHANGE BIASED SINGLE AND DOUBLE TUNNEL JUNCTIONS", Vol. 39, pgs. L1035-L1038, Jpn. J. Appl. Phys., 2000					<input type="checkbox"/> Additional References sheet(s) attached
Examiner					Date Considered		
<p>*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>							

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yoshiaki SAITO, et al.

SERIAL NO: New Application

GAU:

FILED: Herewith

EXAMINER:

FOR: MAGNETIC MEMORY

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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STATEMENT OF RELEVANCY

Reference AA (US 5,659,499) on PTO Form 1449:

This reference shows the similar wiring with ferromagnetic-cladding layer. However, the structure of the ferromagnetic-cladding layer is different from our patent.

Reference AB (US 5,956,267) on PTO Form 1449:

This reference shows the similar wiring with ferromagnetic cladding layer. However, the structure of the ferromagnetic cladding layer is different from our patent.

Reference AE (US 5,940,319) on PTO Form 1449:

This reference shows the similar wiring with ferromagnetic cladding layer. However, the structure of the ferromagnetic cladding layer is different from our patent.

Reference AO (WO 00/10172) on PTO Form 1449:

This reference shows the similar wiring with ferromagnetic cladding layer. However, the structure of the ferromagnetic cladding layer is different from our patent.

Reference AP (JP 10-4227) on PTO Form 1449:

This reference shows RAM having magnetic tunneling junction element.

Reference AR (DE 197 44 095) on PTO Form 1449:

This reference shows a magnetic random access memory having a MOSFET.